

	No.820D	<h1 style="margin: 0;">DRA8</h1> <p style="margin: 0;">Silicon Diffused Junction Type</p> <h2 style="margin: 0;">8.0A Reverse Blocking Thyristor</h2>
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Features

- Glass passivation for high reliability
- Peak OFF-state (reverse) voltage : - 100 to - 600V
- Average ON-state current : 8A
- TO-220 package
- Weight : 2g

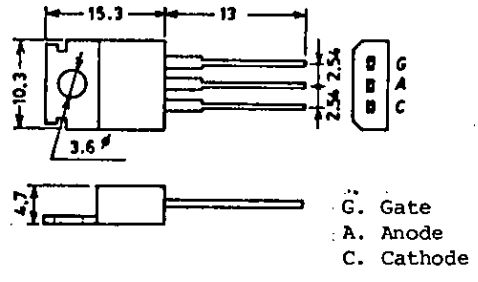
Absolute Maximum Ratings at Ta= 25°C

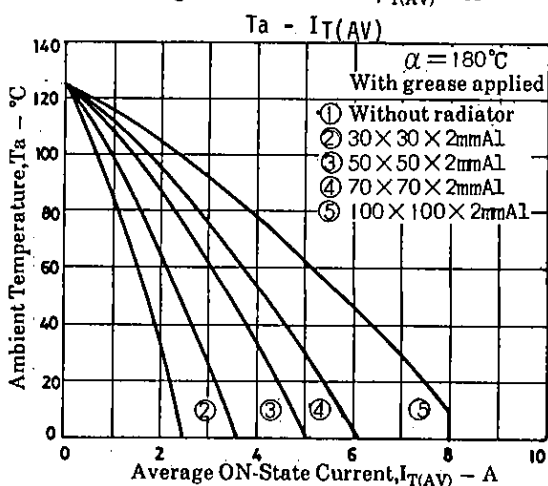
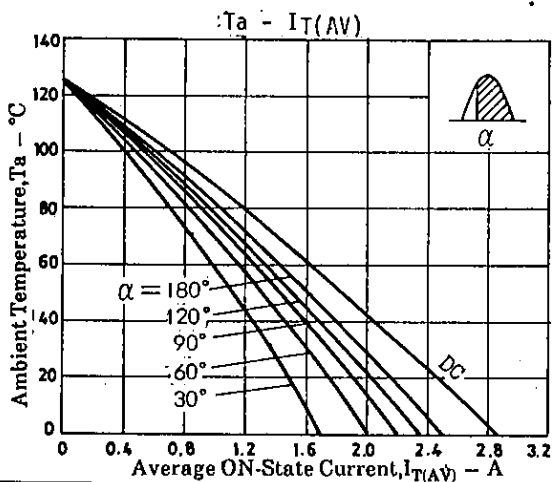
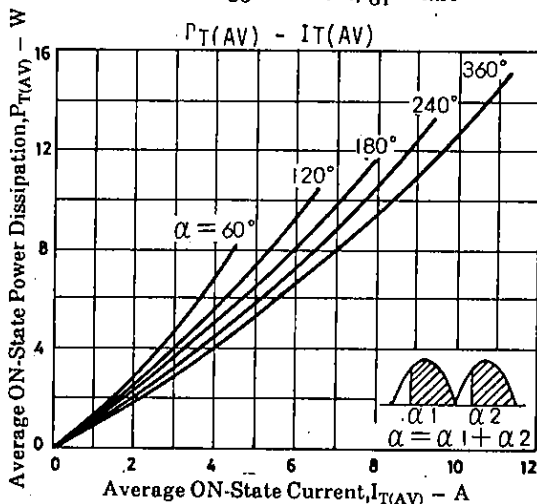
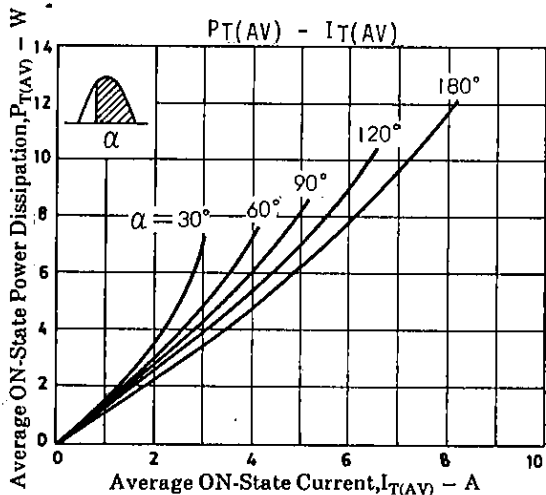
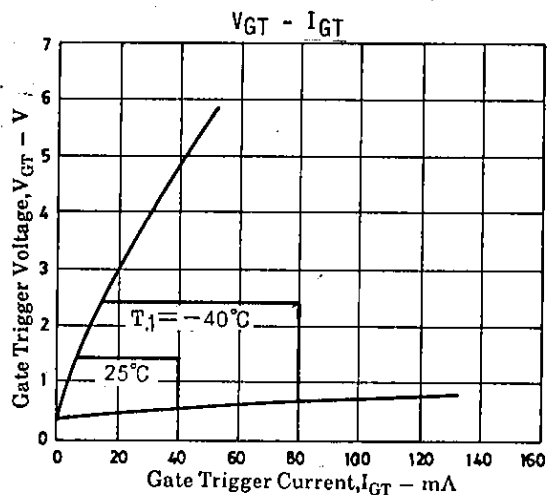
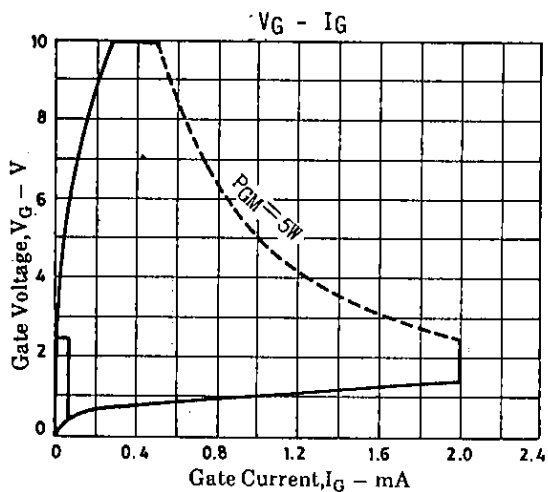
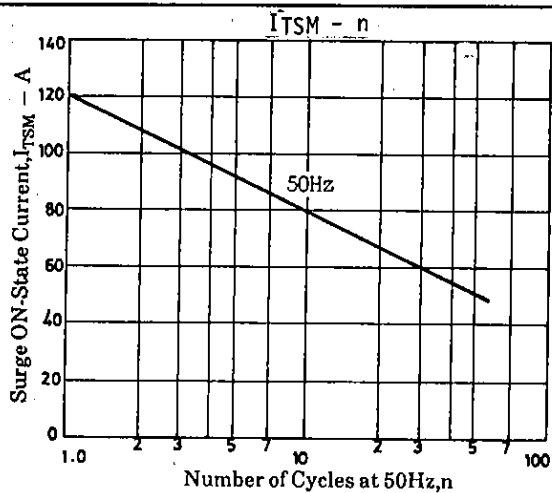
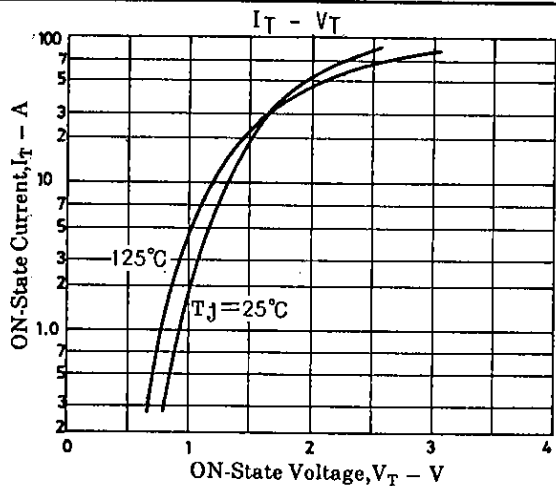
		DRA8B	DRA8C	DRA8E	DRA8G	unit	
Repetitive Peak OFF-State Voltage	V_{DRM}	100	200	400	600	V	
Non-Repetitive Peak Reverse Voltage	V_{RSM}	-150	-300	-500	-700	V	
Repetitive Peak Reverse Voltage	V_{RRM}	-100	-200	-400	-600	V	
Average ON-State Current	$I_{T(AV)}$	Tc= 83°C, single-phase half-wave				8	A
RMS ON-State Current	$I_{T(RMS)}$	→				12.6	A
Surge ON-State Current	I_{TSM}	→				120	A
		Sine half-wave 1 cycle, 50Hz					
Amperes Squared-Seconds	$\int I_T^2 \cdot dt$	→				70	A ² S
Peak Gate Power Dissipation	P_{GM}	→				5	W
Average Gate Power Dissipation	$P_{G(AV)}$	→				0.5	W
Peak Gate Forward Current	I_{FGM}	→				2	A
Peak Gate Forward Voltage	V_{FGM}	→				10	V
Peak Gate Reverse Voltage	V_{RGM}	→				5	V
Junction Temperature	T_j	→				125	°C
Storage Temperature	T_{stg}	→				-40 to +125	°C

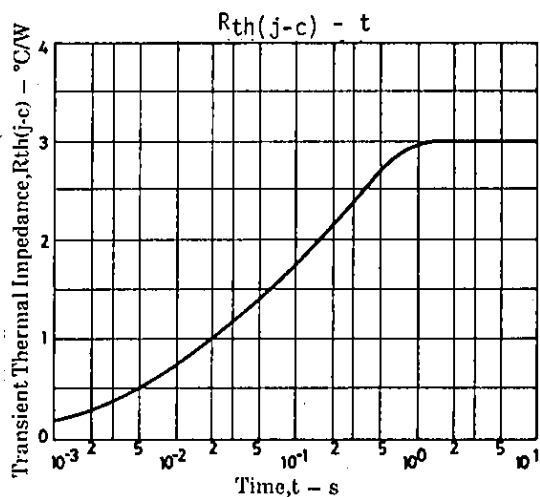
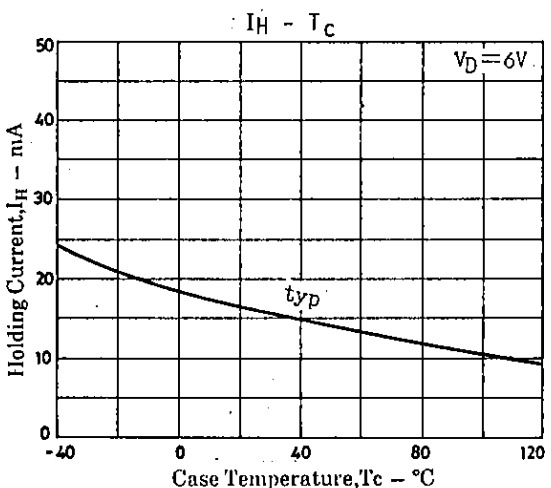
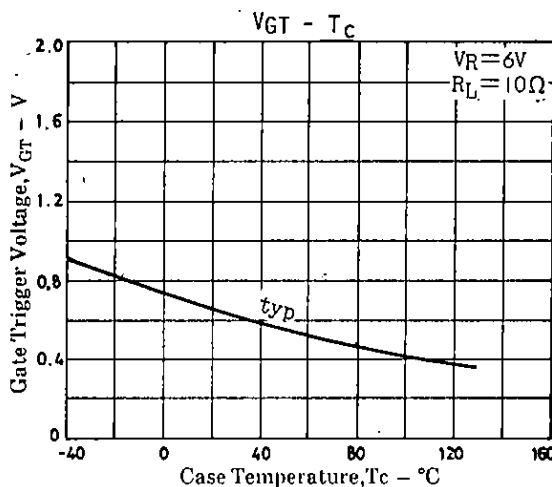
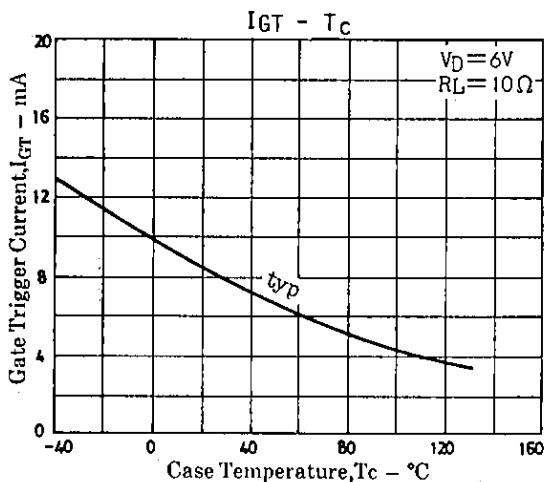
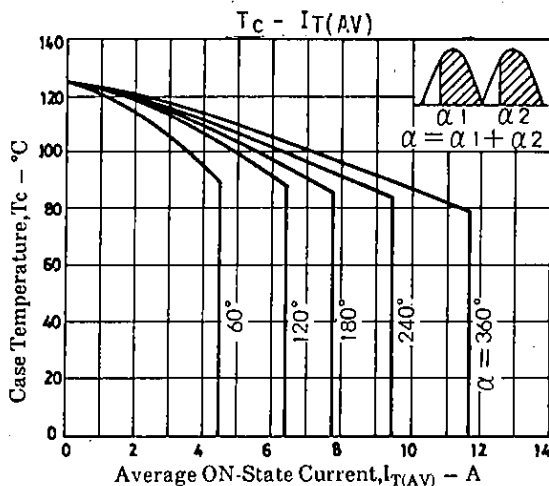
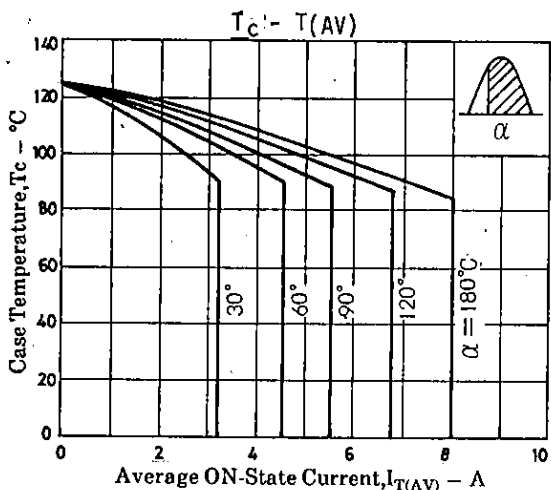
Electrical Characteristics at Ta= 25°C

			min	typ	max	unit
Repetitive Peak OFF-State Current	I_{DRM}	Tj= 125°C, $V_D = V_{DRM}$			2	mA
Repetitive Peak Reverse Current	I_{RRM}	Tj= 125°C, $V_D = V_{RRM}$			2	mA
ON-State Voltage	V_T	$I_T = 25A$			1.6	V
Critical Rate of Rise of OFF-State Voltage	dv/dt	Tc= 125°C, $V_D = 2/3V_{DRM}$	30			V/ μ s
Holding Current	I_H	$R_L = 100\Omega$			60	mA
Gate Trigger Current	I_{GT}	$V_D = 6V, R_L = 10\Omega$			40	mA
Gate Trigger Voltage	V_{GT}	$V_D = 6V, R_L = 10\Omega$			1.5	V
Gate Nontrigger Voltage	V_{GD}	Ta= 125°C, $V_D = 2/3V_{DRM}$	0.2			V
Thermal Resistance	$R_{th(j-c)}$				3	°C/W

Package Dimensions 1104
(unit: mm)







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